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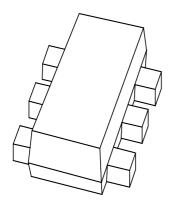
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Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# BC857BV PNP general purpose double transistor

Product data sheet Supersedes data of 2001 Aug 10 2001 Nov 07



# PNP general purpose double transistor

**BC857BV** 

### **FEATURES**

- 300 mW total power dissipation
- · Excellent coplanarity due to straight leads
- Improved thermal behaviour due to flat leads
- Reduces number of components as replacement of two SC-75/SC-89 packaged BISS transistors
- · Reduces required board space
- · Reduces pick and place costs.

# **APPLICATIONS**

• General purpose switching and amplification.

### **DESCRIPTION**

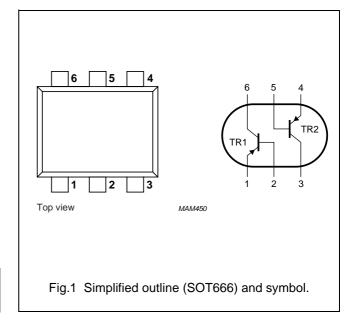
PNP double transistor in a SOT666 plastic package. NPN complement: BC847BV.

# **MARKING**

TYPE NUMBER	MARKING CODE		
BC857BV	3F		

### **PINNING**

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



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# PNP general purpose double transistor

BC857BV

# **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor					
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V	
$V_{CEO}$	collector-emitter voltage	open base	_	-45	V	
V <sub>EBO</sub>	emitter-base voltage	open collector	_	-5	V	
I <sub>C</sub>	collector current (DC)		-	-100	mA	
I <sub>CM</sub>	peak collector current		-	-200	mA	
I <sub>BM</sub>	peak base current		-	-200	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	-	200	mW	
T <sub>stg</sub>	storage temperature		-65	+150	°C	
Tj	junction temperature		-	150	°C	
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C	
Per device	Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	300	mW	

# Note

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th j-a</sub>	thermal resistance from junction to ambient	notes 1 and 2	416	K/W	

### **Notes**

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

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<sup>1.</sup> Transistor mounted on an FR4 printed-circuit board.

# PNP general purpose double transistor

BC857BV

# **CHARACTERISTICS**

 $T_{amb}$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transis	Per transistor					
I <sub>CBO</sub>	collector-base cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = -30 V	_	_	-15	nA
		$I_E = 0$ ; $V_{CB} = -30 \text{ V}$ ; $T_j = 150 ^{\circ}\text{C}$	_	_	-5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-	-100	nA
h <sub>FE</sub>	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	200	_	450	
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-655	-750	mV
V <sub>CEsat</sub>	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-	-100	mV
	voltage	$I_C = -100 \text{ mA}$ ; $I_B = -5. \text{ mA}$ ; note 1	_	-	-400	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-755	_	mV
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0$ ; $V_{CB} = -10 \text{ V}$ ; $f = 1 \text{ MHz}$	_	-	2.2	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = -500 \text{ mV}$ ; $f = 1 \text{ MHz}$	_	10	_	pF
f <sub>T</sub>	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	_	_	MHz

# Note

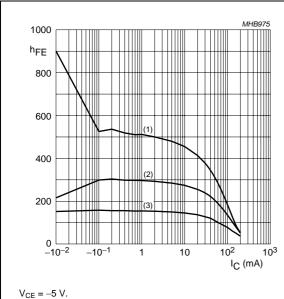
1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

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# PNP general purpose double transistor

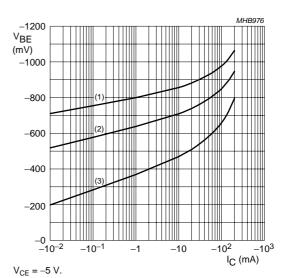
BC857BV

# **Graphical information BC857BV**



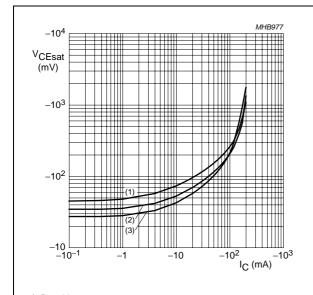
- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.2 DC current gain; typical values.



- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

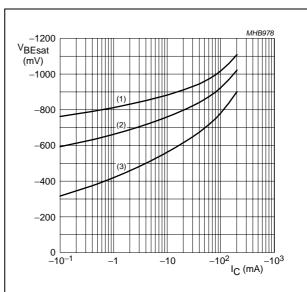
Fig.3 Base-emitter voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 20.$ 

- (1)  $T_{amb} = 150 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = -55 \, ^{\circ}C$ .

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



I<sub>C</sub>/I<sub>B</sub> 20.

- (1)  $T_{amb} = -55 \, ^{\circ}C$ .
- (2)  $T_{amb} = 25 \, ^{\circ}C$ .
- (3)  $T_{amb} = 150 \, ^{\circ}C$ .

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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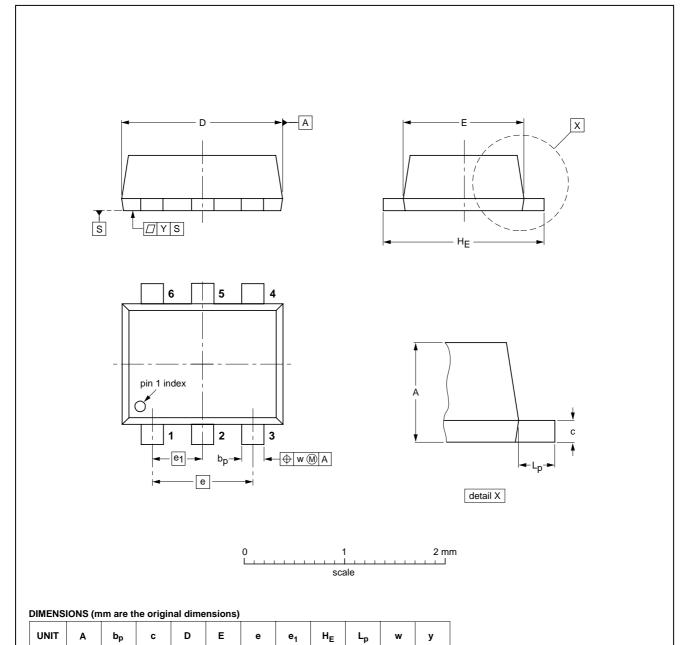
# PNP general purpose double transistor

BC857BV

# **PACKAGE OUTLINE**

Plastic surface mounted package; 6 leads

SOT666



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>01-01-04</del> 01-08-27

0.1

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0.6 0.5

0.27

0.17

0.18

# PNP general purpose double transistor

BC857BV

### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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# **Customer notification**

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# **Contact information**

For additional information please visit: http://www.nxp.com

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